TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

# **TPCC8009**

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance:

 $R_{DS (ON)}$  = 5 m $\Omega$  (typ.) (  $V_{GS}$  = 10 V)

- Low leakage current: I<sub>DSS</sub> = 10 μA (max) (V<sub>DS</sub> = 30 V)
- Enhancement mode:  $V_{th}$  = 2.0 to 3.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

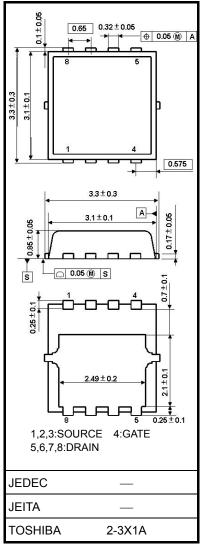
Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Drain-gate voltage (R	k <sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain ourrant	DC (Note 1)	۱ <sub>D</sub>	24	Α	
Drain current	Pulsed (Note 1)	I <sub>DP</sub>	72	А	
Drain power dissipati	on (Tc = 25°C)	PD	27	W	
Drain power dissipati	on (t = 10 s) (Note 2a)	PD	1.9	w	
Drain power dissipation (t = 10 s) (Note 2b)		PD	0.7	w	
Single-pulse avalance	he energy (Note 3)	E <sub>AS</sub>	75	mJ	
Avalanche current		I <sub>AR</sub>	24	A	
Channel temperature	1	T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

Note: For Notes 1 to 3, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

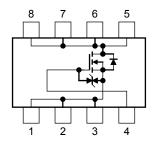
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.02 g (typ.)

#### **Circuit Configuration**

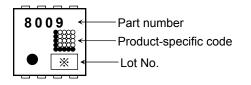


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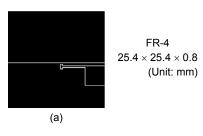
## **Thermal Characteristics**

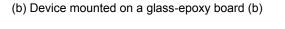
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	4.7	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	66	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	180	°C/W

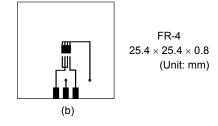
## Marking (Note 4)



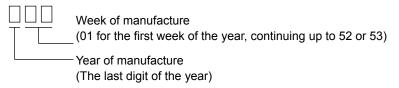
- Note 1: Ensure that the channel temperature does not exceed 150  $^{\circ}\text{C}.$
- Note 2: (a) Device mounted on a glass-epoxy board (a)







- Note 3:  $V_{DD}=24$  V,  $T_{ch}=25^{\circ}C$  (initial),  $L=100~\mu H,~I_{AR}=24$  A
- Note 4: \* Weekly code: (Three digits)



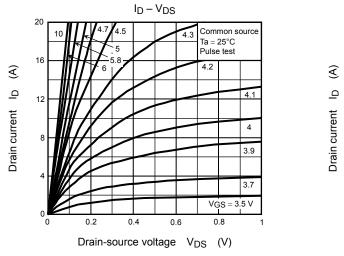
Electrical Characteristics (Ta = 25°C)

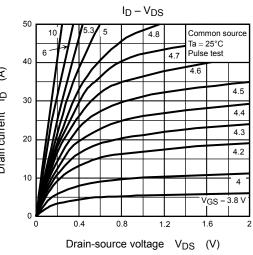
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS}=\pm 16~V,~V_{DS}=0~V$			±10	μA
Drain cutoff curre	ent	IDSS	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Drain agurag bra	ain-source breakdown voltage te threshold voltage ain-source ON-resistance ut capacitance verse transfer capacitance tput capacitance Rise time	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	_	_	V
Drain-source bre	akdown voltage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_	v
Gate threshold ve	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ mA}$	2.0	_	3.0	V
Drain-source ON-resistance		Deserve	$V_{GS} = 6 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		7.2	11	-mΩ
		R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		5	7	
Input capacitance		C <sub>iss</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1 MHz	_	1270		pF
Reverse transfer capacitance		C <sub>rss</sub>		_	230		
Output capacitance		C <sub>oss</sub>		_	360		
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0}V \prod_{V \in S} I_{D} = 12 \text{ A}$	_	6	_	- ns
	Turn-on time	ton			13	_	
	Fall time	t <sub>f</sub>			6	_	
	Turn-off time	t <sub>off</sub>		_	23	_	
Total gate charge (gate-source plus gate-drain)		Qg			26		nC
Gate-source charge 1		Q <sub>gs1</sub>	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 24 A		5		
Gate-drain ("Miller") charge		Q <sub>gd</sub>		—	8.2	—	

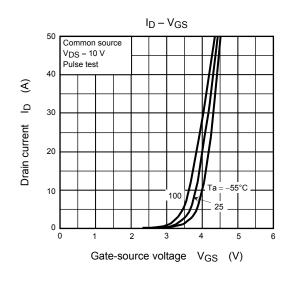
## Source-Drain Ratings and Characteristics (Ta = $25^{\circ}$ C)

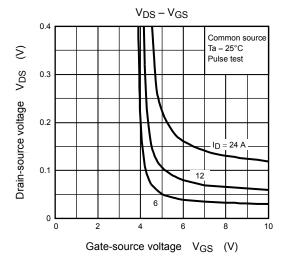
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	—	_	_	72	Α
Forward voltage (diode)			V <sub>DSF</sub>	$I_{DR} = 24 \text{ A}, V_{GS} = 0 \text{ V}$	_		-1.2	V

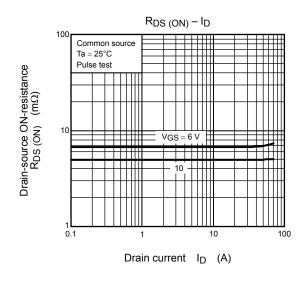
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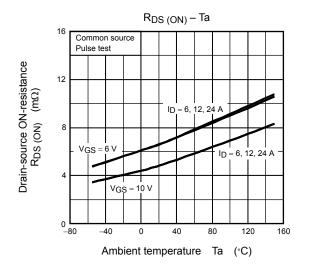


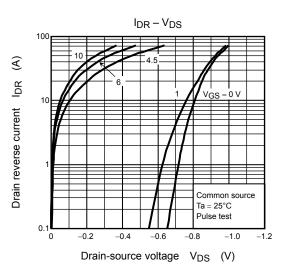


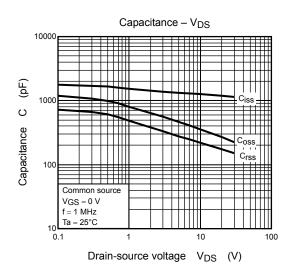


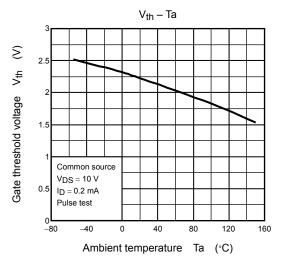


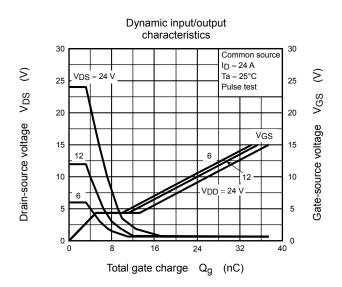
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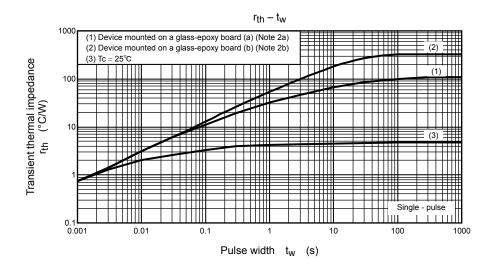


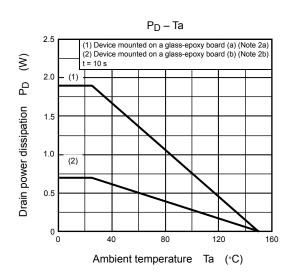


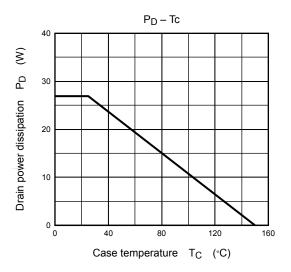


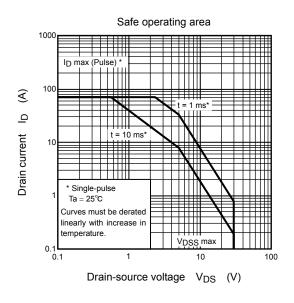












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